Tomohisa Kato

List of Publications by Citations

145 papers	1,259 citations	18 h-index	27 g-index
148 ext. papers	1,512 ext. citations	1.3 avg, IF	4.11 L-index

#	Paper	IF	Citations
145	Correlation between reliability of thermal oxides and dislocations in n-type 4H-SiC epitaxial wafers. *Applied Physics Letters*, **2006**, 89, 022909	3.4	55
144	Growth of Shockley type stacking faults upon forward degradation in 4H-SiC p-i-n diodes. *Journal of Applied Physics*, **2016**, 119, 095711	2.5	53
143	Development of Ultrahigh-Voltage SiC Devices. *IEEE Transactions on Electron Devices*, **2015**, 62, 396-404	2.9	52
142	Growth rate and surface morphology of 4H□SiC crystals grown from Si□Cr□ and Si□Cr□Al□ solutions under various temperature gradient conditions. *Journal of Crystal Growth*, **2014**, 401, 681-685	1.6	50
141	Short minority carrier lifetimes in highly nitrogen-doped 4H-SiC epilayers for suppression of the stacking fault formation in PiN diodes. *Journal of Applied Physics*, **2016**, 120, 115101	2.5	47
140	Entropy change in lithium ion cells on charge and discharge. *Journal of Applied Electrochemistry*, **2002**, 32, 251-258	2.6	45
139	Effect of aluminum addition on the surface step morphology of 4H□SiC grown from Si□Cr□ solution. *Journal of Crystal Growth*, **2015**, 423, 45-49	1.6	33
138	The growth of low resistivity, heavily Al-doped 4H□SiC thick epilayers by hot-wall chemical vapor deposition. *Journal of Crystal Growth*, **2013**, 380, 85-92	1.6	30
137	Injected carrier concentration dependence of the expansion of single Shockley-type stacking faults in 4H-SiC PiN diodes. *Journal of Applied Physics*, **2018**, 123, 025707	2.5	30
136	High Throughput SiC Wafer Polishing with Good Surface Morphology. *Materials Science Forum*, **2007**, 556-557, 753-756	0.4	23
135	Characterization of Electric Discharge Machining for Silicon Carbide Single Crystal. *Materials Science Forum*, **2008**, 600-603, 855-858	0.4	22
134	Determination of Etch Rate Behavior of 4H□SiC Using Chlorine Trifluoride Gas. *Japanese Journal of Applied Physics*, **2007**, 46, 7875-7879	1.4	22
133	Temperature-Dependent Behavior of 4H-Silicon Carbide Surface Morphology Etched Using Chlorine Trifluoride Gas. *Journal of the Electrochemical Society*, **2009**, 156, H971	3.9	21
132	Dependences of contraction/expansion of stacking faults on temperature and current density in 4H-SiC p□□ diodes. *Japanese Journal of Applied Physics*, **2018**, 57, 061301	1.4	20
131	Challenges of High-Performance and High-Reliablity in SiC MOS Structures. *Materials Science Forum* , **2012**, 717-720, 703-708	0.4	19
130	Effects of Dislocations on Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. *Materials Science Forum*, **2005**, 483-485, 661-664	0.4	19
129	Raman characterization of damaged layers of 4H-SiC induced by scratching. *AIP Advances*, **2016**, 6, 015207	1.5	19

128	Determination of carrier concentration by Fano interference of Raman scattering in heavily doped n-type 4H-SiC. *Journal of Applied Physics*, **2012**, 112, 043514	2.5	18
127	Flux-Controlled Sublimation Growth by an Inner Guide-Tube. *Materials Science Forum*, **2002**, 389-393, 83-86	0.4	18
126	Structural analysis of double-layer Shockley stacking faults formed in heavily-nitrogen-doped 4H-SiC during annealing. *Journal of Applied Physics*, **2017**, 122, 045707	2.5	16
125	Growth Rate and Surface Morphology of 4H-SiC Single Crystal Grown under Various Supersaturations Using Si-C Solution. *Materials Science Forum*, **2013**, 740-742, 23-26	0.4	16
124	Determination of free carrier density in the low doping regime of 4H-SiC by Raman scattering. *Applied Physics Letters*, **2008**, 93, 121913	3.4	16
123	In-situ observation of silicon carbide sublimation growth by X-ray topography. *Journal of Crystal Growth*, **2001**, 222, 579-585	1.6	16
122	Influence of basal-plane dislocation structures on expansion of single Shockley-type stacking faults in forward-current degradation of 4H-SiC p□n diodes. *Japanese Journal of Applied Physics*, **2018**, 57, 04FR07	1.4	15
121	Defect and Growth Analysis of SiC Bulk Single Crystals with High Nitrogen Doping. *Materials Science Forum*, **2007**, 556-557, 239-242	0.4	15
120	Growth of P-type 4H□SiC single crystals by physical vapor transport using aluminum and nitrogen co-doping. *Journal of Crystal Growth*, **2017**, 470, 154-158	1.6	14
119	Modification of the surface morphology of 4H-SiC by addition of Sn and Al in solution growth with SiCr solvents. *Journal of Crystal Growth*, **2017**, 458, 37-43	1.6	14
118	Microstructural Analysis of Damaged Layer Introduced during Chemo-Mechanical Polishing. *Materials Science Forum*, **2014**, 778-780, 370-373	0.4	14
117	Cutting Speed of Electric Discharge Machining for SiC Ingot. *Materials Science Forum*, **2012**, 717-720, 861-864	0.4	14
116	High-Quality SiC Bulk Single Crystal Growth Based on Simulation and Experiment. *Materials Science Forum*, **2004**, 457-460, 29-34	0.4	14
115	Quantitative Analysis of Nanoscale Step Dynamics in High-Temperature Solution-Grown Single Crystal 4H-SiC via In Situ Confocal Laser Scanning Microscope. *Crystal Growth and Design*, **2017**, 17, 2844-2851	3.5	12
114	Observation of double Shockley stacking fault expansion in heavily-nitrogen-doped 4H-SiC using PL technique. *Journal of Crystal Growth*, **2017**, 468, 889-893	1.6	12
113	The photoelastic constant and internal stress around micropipe defects of 6H-SiC single crystal. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 57, 147-149	3.1	12
112	Micro-structural analysis of local damage introduced in subsurface regions of 4H-SiC wafers during chemo-mechanical polishing. *Journal of Applied Physics*, **2016**, 119, 135702	2.5	11
111	Reliability of Gate Oxides on 4H-SiC Epitaxial Surface Planarized by CMP Treatment. *Materials Science Forum*, **2014**, 778-780, 545-548	0.4	11

110	Origin analysis of expanded stacking faults by applying forward current to 4H-SiC pin diodes. *Applied Physics Express*, **2017**, 10, 081201	2.4	11
109	Reducing Stacking Faults in Highly Doped N-Type 4H-SiC Crystal. *Materials Science Forum*, **2011**, 679-680, 8-11	0.4	11
108	4H-SiC Growth from Si-Cr-C Solution under Al and N Co-Doping Conditions. *Materials Science Forum*, **2015**, 821-823, 9-13	0.4	10
107	Dynamic characteristics of large current capacity module using 16-kV ultrahigh voltage SiC flip-type n-channel IE-IGBT **2014**,		10
106	Electric Discharge Machining for Silicon Carbide and Related Materials. *Materials Science Forum*, **2008**, 600-603, 851-854	0.4	10
105	4H Silicon Carbide Etching Using Chlorine Trifluoride Gas. *Materials Science Forum*, **2008**, 600-603, 655-658	0.4	10
104	Deep Ultraviolet Raman Microspectroscopic Characterization of Polishing-Induced Surface Damage in SiC Crystals. *Journal of the Electrochemical Society*, **2006**, 153, G319	3.9	10
103	4H-SiC Surface Morphology Etched Using ClF3 Gas. *Materials Science Forum*, **2010**, 645-648, 787-790	0.4	9
102	SiC Single Crystal Growth Rate Measurement by In-Situ Observation using the Transmission X-Ray Technique. *Materials Science Forum*, **2000**, 338-342, 75-78	0.4	9
101	Relationship between depth of basal-plane dislocations and expanded stacking faults by application of forward current to 4H-SiC p-i-n diodes. *Applied Physics Express*, **2019**, 12, 051007	2.4	8
100	Control of temperature distribution to suppress macro-defects in solution growth of 4H-SiC crystals. *Journal of Crystal Growth*, **2019**, 523, 125151	1.6	8
99	Etching Rate Behavior of 4H-Silicon Carbide Using Chlorine Trifloride Gas. *ECS Transactions*, **2008**, 13, 39-52	1	8
98	Observation of surface polarity dependent phonons in SiC by deep ultraviolet Raman spectroscopy. *Physical Review B*, **2007**, 75,	3.3	8
97	Dependence of conduction mechanisms in heavily Al-doped 4H-SiC epilayers on Al concentration. *Applied Physics Express*, **2018**, 11, 101302	2.4	8
96	Chlorine Trifluoride Gas Transport and Etching Rate Distribution in Silicon Carbide Dry Etcher. *Materials Science Forum*, **2015**, 821-823, 553-556	0.4	7
95	Transition of conduction mechanism from band to variable-range hopping conduction due to Al doping in heavily Al-doped 4H-SiC epilayers. *Japanese Journal of Applied Physics*, **2019**, 58, 098004	1.4	7
94	Effects of Al addition to Si-based flux on the growth of 4H-SiC films by vapour–liquid–solid pulsed laser deposition. *CrystEngComm*, **2017**, 19, 5188-5193	3.3	7
93	Density of Etch Pits on C-Face 4H-SiC Surface Produced by ClF3 Gas. *Materials Science Forum*, **2012**, 725, 49-52	0.4	7

92	Investigation of In-Grown Dislocations in 4H-SiC Epitaxial Layers. *Materials Science Forum*, **2006**, 527-529, 147-152	0.4	7
91	Large Diameter and Long Length Growth of SiC Single Crystal. *Materials Science Forum*, **2004**, 457-460, 99-102	0.4	7
90	Dislocation constraint by etch back process of seed crystal in the SiC sublimation growth. *Journal of Crystal Growth*, **2001**, 233, 219-225	1.6	7
89	Numerical Simulation of Heat and Mass Transfer in SiC Sublimation Growth. *Materials Science Forum* , **2002**, 389-393, 43-46	0.4	7
88	In situ x-ray topography of silicon carbide during crystal growth by sublimation method. *Review of Scientific Instruments*, **2000**, 71, 2829-2832	1.7	7
87	Difference of double Shockley-type stacking faults expansion in highly nitrogen-doped and nitrogen-boron co-doped n-type 4H-SiC crystals. *Journal of Crystal Growth*, **2017**, 468, 879-882	1.6	6
86	Expansion and contraction of single Shockley stacking faults in SiC epitaxial layer under ultraviolet irradiation. *Applied Physics Express*, **2019**, 12, 041006	2.4	6
85	Growth Study of p-Type 4H-SiC with Using Aluminum and Nitrogen Co-Doping by 2-Zone Heating Sublimation Method. *Materials Science Forum*, **2015**, 821-823, 47-50	0.4	6
84	Uniform growth of SiC single crystal thin films via a metal–Si alloy flux by vapour–liquid–solid pulsed laser deposition: the possible existence of a precursor liquid flux film. *CrystEngComm*, **2016**, 18, 143-148	3.3	6
83	Comparison of Conduction Mechanisms in Heavily Al-Doped 4H-SiC and Heavily Al- and N-Codoped 4H-SiC. *Materials Science Forum*, **2018**, 924, 188-191	0.4	6
82	Glide velocities of Si-core partial dislocations for double-Shockley stacking fault expansion in heavily nitrogen-doped SiC during high-temperature annealing. *Journal of Applied Physics*, **2018**, 124, 025705	2.5	6
81	Local Strain Distribution and Microstructure of Grinding-Induced Damage Layers in SiC Wafer. *Journal of Electronic Materials*, **2018**, 47, 6722-6730	1.9	6
80	Growth of Low Resistivity n-Type 4H-SiC Bulk Crystals by Sublimation Method Using Co-Doping Technique. *Materials Science Forum*, **2014**, 778-780, 47-50	0.4	6
79	Mirror Etching of Single Crystalline C-Face 4H-Silicon Carbide Wafer by Chlorine Trifluoride Gas. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P582-P585	2	6
78	Development of Silicon Carbide Dry Etcher Using Chlorine Trifluoride Gas. *Materials Science Forum*, **2014**, 778-780, 738-741	0.4	6
77	High-throughput screening of Si-Ni flux for SiC solution growth using a high-temperature laser microscope observation and secondary ion mass spectroscopy depth profiling. *ACS Combinatorial Science*, **2013**, 15, 287-90	3.9	6
76	Electric Discharge Machining for Silicon Carbide in Gases of Ar, Ar-CH4 and Ar-CF4 Mixtures. *Materials Science Forum*, **2010**, 645-648, 869-872	0.4	6
75	Density and Behavior of Etch Pits on C-Face 4H-SiC Surface Produced by CIF3 Gas. *Materials Science Forum*, **2012**, 717-720, 379-382	0.4	6

74	Effect of heat transfer on macroscopic and microscopic crystal quality in silicon carbide sublimation growth. *Journal of Crystal Growth*, **2007**, 303, 342-344	1.6	6
73	Demonstration of motor drive with SiC normally-off IBMOSFET/SBD power converter **2007**,		6
72	Stress Analysis of SiC Bulk Single Crystal Growth by Sublimation Method. *Materials Science Forum*, **2003**, 433-436, 13-16	0.4	6
71	Application of Defect Conversion Layer by Solution Growth for Reduction of TSDs in 4H-SiC Bulk Crystals by PVT Growth. *Materials Science Forum*, **2019**, 963, 71-74	0.4	5
70	Change in Surface Morphology by Addition of Impurity Elements in 4H-SiC Solution Growth with Si Solvent. *Materials Science Forum*, **2015**, 821-823, 14-17	0.4	5
69	Characterization of double Shockley-type stacking faults formed in lightly doped 4H-SiC epitaxial films. *Journal of Crystal Growth*, **2018**, 490, 89-96	1.6	5
68	Growth of Low Resistivity p-Type 4H-SiC Crystals by Sublimation with Using Aluminum and Nitrogen Co-Doping. *Materials Science Forum*, **2016**, 858, 77-80	0.4	5
67	High-Speed Slicing of SiC Ingot by High-Speed Multi Wire Saw. *Materials Science Forum*, **2014**, 778-780, 771-775	0.4	5
66	13-kV, 20-A 4H-SiC PiN Diodes for Power System Applications. *Materials Science Forum*, **2014**, 778-780, 855-858	0.4	5
65	Morphology Improvement of Step Bunching on 4H-SiC Wafers by Polishing Technique. *Materials Science Forum*, **2010**, 645-648, 763-765	0.4	5
64	Spectroscopic Measurement of Electric Discharge Machining for Silicon Carbide. *Materials Science Forum*, **2009**, 615-617, 609-612	0.4	5
63	Initiation of Shockley Stacking Fault Expansion in 4H-SiC P-i-N Diodes. *Materials Science Forum*, **2019**, 963, 280-283	0.4	5
62	Reduction of threading screw dislocations in 4H-SiC crystals by a hybrid method with solution growth and physical vapor transport growth. *Journal of Crystal Growth*, **2021**, 568-569, 126189	1.6	5
61	Morphological stability of 4H-SiC crystals in solution growth on {0001} and {11 0m} surfaces. *Journal of Crystal Growth*, **2017**, 468, 883-888	1.6	4
60	Temperature dependence of double Shockley stacking fault behavior in nitrogen-doped 4H-SiC studied by in-situ synchrotron X-ray topography. *Acta Materialia*, **2020**, 194, 387-393	8.4	4
59	Evaluation of the increase in threading dislocation during the initial stage of physical vapor transport growth of 4H-SiC. *Japanese Journal of Applied Physics*, **2018**, 57, 065501	1.4	4
58	Development of Multi-Wire Electric Discharge Machining for SiC Wafer Processing. *Materials Science Forum*, **2014**, 778-780, 776-779	0.4	4
57	AlN bulk crystal growth by sublimation method. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 1775-1777		4

56	Growth and Evaluation of High Quality SiC Crystal by Sublimation Method. *Materials Science Forum*, **2002**, 389-393, 87-90	0.4	4
55	In-situ Observation of SiC Bulk Single Crystal Growth by X-Ray Topography. *Materials Science Forum*, **2000**, 338-342, 457-460	0.4	4
54	Structural analysis of interfacial dislocations and expanded single Shockley-type stacking faults in forward-current degradation of 4H-SiC p-i-n diodes. *Japanese Journal of Applied Physics*, **2019**, 58, 011005	1.4	4
53	Effect of Forced Convection by Crucible Design in Solution Growth of SiC Single Crystal. *Materials Science Forum*, **2015**, 821-823, 22-25	0.4	3
52	Formation and Removal of Carbon Film on Silicon Carbide Surface Using Chlorine Trifluoride Gas. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P441-P445	2	3
51	Development of Large SiC Wafer Processing Technique in ^|^ldquo;Novel Semiconductor Power Electronics Project Realizing Low Carbon Emission Society^|^rdquo; Supported by NEDO. *Journal of the Japan Society for Precision Engineering*, **2014**, 80, 18-22	0.1	3
50	Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers. *Materials Science Forum*, **2014**, 778-780, 151-154	0.4	3
49	Slicing of Rotating SiC Ingot by Electric Discharge Machining. *Materials Science Forum*, **2013**, 740-742, 843-846	0.4	3
48	Enlargement Growth of Large 4H-SiC Bulk Single Crystal. *Materials Science Forum*, **2011**, 679-680, 3-7	0.4	3
47	Thermoelectric Properties of Single-Crystalline SiC and Dense Sintered SiC for Self-Cooling Devices. *Japanese Journal of Applied Physics*, **2011**, 50, 031301	1.4	3
46	Development of New Complex Machining Technology for Single Crystal Silicon Carbide Polishing. *International Journal of Automation Technology*, **2016**, 10, 786-793	0.8	3
45	Relationship between Temperature Dependencies of Resistivity and Hall Coefficient in Heavily Al-Doped 4H-SiC Epilayers. *Materials Science Forum*, **2019**, 963, 324-327	0.4	3
44	Observation of multilayer Shockley-type stacking fault formation during process of epitaxial growth on highly nitrogen-doped 4H-SiC substrate. *Japanese Journal of Applied Physics*, **2019**, 58, 021001	1.4	3
43	Platinum additive impacts on vapor-liquid-solid growth chemical interface for high-quality SiC single crystal films. *Materials Today Chemistry*, **2020**, 16, 100266	6.2	2
42	Sign of Hall coefficient in nearest-neighbor hopping conduction in heavily Al-doped p-type 4H-SiC. *Japanese Journal of Applied Physics*, **2020**, 59, 051004	1.4	2
41	Effect of Al addition to Si–Ni flux on pulsed laser deposition of SiC thin films. *Journal of the Ceramic Society of Japan*, **2016**, 124, 506-509	1	2
40	Influence of Additives on Surface Smoothness and Polytype Stability in Solution Growth of n-Type 4H-SiC. *Materials Science Forum*, **2018**, 924, 55-59	0.4	2
39	Immobilization Phenomenon of Partials Surrounding Double Shockley Stacking Faults in Heavily Nitrogen Doped 4H-SiC Crystal with Thermal Anneal. *Materials Science Forum*, **2018**, 924, 160-163	0.4	2

38	Development of ultrahigh voltage SiC power devices **2014**,		2
37	Growth of 4H-SiC in Current-Controlled Liquid Phase Epitaxy. *Materials Science Forum*, **2013**, 740-742, 3-6	0.4	2
36	Ultrahigh voltage SiC bipolar devices **2013**,		2
35	Control of Void Formation in 4H-SiC Solution Growth. *Materials Science Forum*, **2012**, 717-720, 57-60	0.4	2
34	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. *Journal of Applied Physics*, **2020**, 128, 105702	2.5	2
33	Massive reduction of threading screw dislocations in 4H-SiC crystals grown by a hybrid method combined with solution growth and physical vapor transport growth on higher off-angle substrates. *Applied Physics Express*, **2021**, 14, 085506	2.4	2
32	Chlorine Trifluoride Gas Distributor Design for Single-Crystalline C-Face 4H-Silicon Carbide Wafer Etcher. *Materials Science Forum*, **2019**, 963, 520-524	0.4	2
31	Crystal growth and evaluation of nitrogen and aluminum co-doped N-type 4H-SiC grown by physical vapor transport. *Journal of Crystal Growth*, **2018**, 498, 224-229	1.6	2
30	Etching Rate Profile of C-Face 4H-SiC Wafer Depending on Total Gas Flow Rate of Chlorine Trifluoride and Nitrogen. *Materials Science Forum*, **2020**, 1004, 173-179	0.4	1
29	Anomalous Temperature Dependence of the Hall Coefficient of Heavily Al-Doped 4H-SiC Epilayers in the Band Conduction Region. *Materials Science Forum*, **2020**, 1004, 215-223	0.4	1
28	Characterization of stacking faults with emission wavelengths of over 500 nm formed in 4H-SiC epitaxial films. *Journal of Crystal Growth*, **2017**, 476, 99-106	1.6	1
27	Effects of Machining Fluid on Electric Discharge Machining of SiC Ingot. *Materials Science Forum*, **2014**, 778-780, 767-770	0.4	1
26	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. *ECS Journal of Solid State Science and Technology*, **2013**, 2, N3025-N3027	2	1
25	AlN bulk single crystal growth on SiC and AlN substrates by sublimation method **2010**,		1
24	Etch Pits on 4H-SiC Surface Produced by ClF3 Gas. *Materials Science Forum*, **2011**, 679-680, 286-289	0.4	1
23	Effect of Radiation in Solid during SiC Sublimation Growth. *Materials Research Society Symposia Proceedings*, **2006**, 911, 2		1
22	Influence of Micropipe and Domain Boundary in SiC Substrate on the DC Characteristics of AlGaN/GaN HFET. *Materials Science Forum*, **2007**, 556-557, 1043-1046	0.4	1
21	Characterization of Inclusions in SiC Bulk Crystals Grown by Modified Lely Method. *Materials Science Forum*, **2002**, 389-393, 75-78	0.4	1

20	Dislocation Constraint by Etch-Back Process of Seed Crystal in SiC Bulk Crystal Growth. *Materials Science Forum*, **2002**, 389-393, 111-114	0.4	1
19	X-ray Topographic Study of SiC Crystal at High Temperature. *Materials Science Forum*, **2000**, 338-342, 461-464	0.4	1
18	Direct visualization of kinetic reversibility of crystallization and dissolution behavior at solution growth interface of SiC in Si-Cr solvent. *Surfaces and Interfaces*, **2022**, 28, 101664	4.1	1
17	4H-Silicon Carbide Wafer Surface after Chlorine Trifluoride Gas Etching. *Materials Science Forum*, **2018**, 924, 369-372	0.4	1
16	Non-Plasma Dry Etcher Design for 200 mm-Diameter Silicon Carbide Wafer. *Materials Science Forum* , **2020**, 1004, 167-172	0.4	0
15	Immobilization of partial dislocations bounding double Shockley stacking faults in 4H-SiC observed by in situ synchrotron X-ray topography. *Materialia*, **2021**, 20, 101246	3.2	0
14	Nondestructive measurements of depth distribution of carrier lifetimes in 4H-SiC thick epitaxial layers using time-resolved free carrier absorption with intersectional lights. *Review of Scientific Instruments*, **2020**, 91, 123902	1.7	0
13	Modulation of Growth Rate by Electric Current in Liquid-Phase Epitaxy of 4H-SiC. *Japanese Journal of Applied Physics*, **2013**, 52, 085503	1.4	0
12	Polarity Inversion of SiC(0001) during the Al Doped PVT Growth. *Materials Science Forum*, **2015**, 821-823, 73-76	0.4	
11	Anomalous Conduction between the Band and Nearest-Neighbor Hopping Conduction Regions in Heavily Al-Doped p-Type 4H-SiC. *Materials Science Forum*, **2020**, 1004, 224-230	0.4	
10	Low V F 4H-SiC N-i-P diodes using newly developed low-resistivity p-type substrates. *Japanese Journal of Applied Physics*, **2020**, 59, SGGD14	1.4	
9	Etch Pits of 4H-Silicon Carbide Surface Formed Using Chlorine Trifluoride Gas. *ECS Transactions*, **2010**, 28, 81-88	1	
8	Defect Characterization of 4H-SiC Bulk Crystals Grown on Micropipe Filled Seed Crystals. *Materials Science Forum*, **2005**, 483-485, 315-318	0.4	
7	Defect Analysis of SiC Sublimation Growth by the In-Situ X-Ray Topography. *Materials Science Forum*, **2001**, 353-356, 295-298	0.4	
6	Silicon carbide epitaxial layer growths on Acheson seed crystals from silicon melt. *Materials Letters*, **2002**, 57, 307-314	3.3	
5	New Crucible Design for SiC Single Crystal Growth by Sublimation. *Materials Research Society Symposia Proceedings*, **2000**, 640, 1		
4	Depth Distribution of Defects in SiC PiN Diodes Formed Using Ion Implantation or Epitaxial Growth. *Physica Status Solidi (B): Basic Research*,2100419	1.3	
3	Formation of Double Shockley Stacking Faults in Heavily Nitrogen Doped 4H-SiC Crystal with Reduction of Residual Stress around Scratch Damage. *Materials Science Forum*, **2020**, 1004, 427-432	0.4	

2	Simple physical model for the sign of the Hall coefficient in variable-range hopping conduction in heavily Al-doped p-type 4H-SiC. *Japanese Journal of Applied Physics*, **2021**, 60, 031008	1.4
1	Vapor–liquid–solid growth of 4H-SiC single crystal films with extremely low carrier densities in chemical vapor deposition with a Pt–Si alloy flux and X-ray topography analysis of their dislocation propagation behaviors. *CrystEngComm*, **2021**, 23, 5039-5044	3.3